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6.622 Power Electronics

Lecture 7 — DC/DC Lecture 3

1 Converters

Consider device and passive component ratings of converters:





For now, assume L, C <u>big</u> $i_L \approx I_L, v_c \approx V_c$

$$I_L = |I_1| + |I_2|$$
$$V_c = |V_1| + |V_2|$$

So we have	$v_{sw,max} = v_{d,max} = v_c = V_1 + V_2 $
	$i_{sw,max} = i_{d,max} = I_L = I_1 + I_2 $

Let's look at direct converters (L, C: <u>big</u>: $i_L \approx I_L, v_c \approx V_c$)





So based on device and passive component stresses, we would choose a direct converter over an indirect converter whenever possible!

In practice, component election does depend on ripple in many classes. Let's see how to <u>approximately</u> calculate ripple effects.

To calculate capacitor voltage ripple, we:

- 1. Neglect ripple in inductor (assume $L \approx \inf$ so $\Delta i_{2,pp} \approx 0$)
- 2. assume <u>all</u> current voltage ripple goes into capacitor
- 3. calculate voltage ripple
- 4. verify assumption afterward

Ex: Boost converter ripple



So we model the system assuming all <u>ripple</u> current component (\tilde{i}_d) goes into the capacitor, and the old dc component $\langle i_d \rangle$ goes into the resistor. For this to be true, $2\pi f_{sw} \gg \frac{1}{RC}$

Under this assumption, a "ripple only" model is:



- ripple in v_c is triangular
- the average value of a Δ wave is half-way between its peaks, so we get ripple between $\pm \delta \frac{v_{c,pp}}{2}$

$$i = c \frac{dv_c}{dt} \to \Delta v_c = \frac{1}{c} \int i_c dt$$

$$\underbrace{D(1-D)I_LT}_{C}$$
where $I_L = I_1$

$$\Delta v_{c,pp} = \frac{D(1-D)I_LT}{C} \qquad \text{where } I_L = I$$

So to limit ripple to be low a specified value

$$C \ge \frac{D(1-D)I_1T}{\Delta v_{c,m}}$$

Similar calculations can be made for current ripple in i_L .



The flat black line says: neglecting capacitor voltage ripple (a good approximation) Blue line says: real case (is ∞ with ripple calculated above)



neglecting $z_x, v_L = -\hat{v}_x$ (On right arrow: Neglecting any drop on z_i)



So from our previous results

$$L \ge \frac{D(1-D)Tv_2}{2I_1R_L} \qquad \qquad C \ge \frac{D(1-D)I_1T}{2V_cR_c}$$

Energy storage is one metric for the minimum size of an energy storage component. What is required energy storage?

Capacitor:

$$E_{c} = \frac{1}{2}CV_{c,pk}^{2}$$

$$= \frac{1}{2}\frac{D(1-D)I_{1}T}{2V_{c}R_{c}}[V_{c}(1+R_{c})]^{2}$$

$$\frac{1}{2}\frac{D(I_{1}V_{1})T}{2}\frac{(1+R_{c})^{2}}{R_{c}}$$

$$E_{c} = \frac{DTP_{0}}{4}\frac{(1+R_{c})^{2}}{R_{c}}$$

So energy storage increases with

- 1. switching period
- 2. output power
- 3. conversion ratio
- 4. <u>smaller</u> ripple spec (? cannot read space or spec)

Similar arguments for inductor $E_L = \frac{DP_0}{4f_{sw}} \frac{(1+R_c)^2}{R_c}$ It can be shown that direct converters always require less energy storage (+ hence smaller components) than indirect converters.

We can also factor in ripple on our peak device stresses: DIRECT:

$$v_{c,pk} = v_{sw,pk} = v_{d,pk} = max(|v_1|, |v_2|)(1 + R_c)$$
$$i_{L,pk} = i_{sw,pk} = i_{d,pk} = max(|I_1|, |I_2|)(1 + R_2)$$
$$v_{c,pk} = v_{sw,pk} = v_{d,pk} = (|v_1| + |v_2|)(1 + R_c)$$

INDIRECT:

$$v_{c,pk} = v_{sw,pk} = v_{d,pk} = (|v_1| + |v_2|)(1 + R_c)$$
$$i_{L,pk} = i_{sw,pk} = i_{d,pk} = (|I_1| + |I_2|)(1 + R_2)$$

If time, define metric for switch size: switch stress parameter S.S.P. $\stackrel{\Delta}{=} V_{sw,pk} * i_{sw,pk}$

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